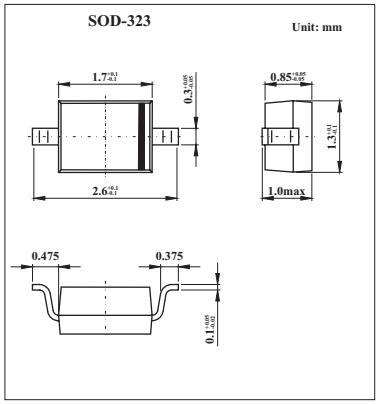
Silicon Schottky Diode

BAT68-03W



■ Features

- For mixer applications in the VHF/UHF range
- For high speed switching

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	8	V
Forward current	I_F	130	mA
Total Power dissipation TS = 95 ℃	P_{tot}	150	mW
Junction temperature	Tj	150	℃
Operating temperature range	T_{op}	-65 to +150	℃
Storage temperature	T_{stg}	-65 to +150	℃
Junction ambient	R_{thJA}	445	K/W
Junction - soldering point	R_{thJS}	365	K/W

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	$V_{(BR)}$	$I_{(BR)}$ = 10 μ A	8			V
Reverse current	I_R	V_R = 1 V, T_A = 25℃			0.1	μ A
		V_R = 1 V, T_A = 60℃			1.2	
Forward voltage	V_F	I_F = 1 mA		318	340	mV
		I_F = 10 mA	340	390	500	
Diode capacitance	C_T	V_R = 0 V, f = 1 MHz			1	pF
Differential forward resistance	R_F	I_F = 5 mA			10	Ω

Forward current I_F = f (TA*; TS)

*): mounted on alumina 15mm x 16.7mm x 0.7mm

■ Marking

Marking	K